Abstracts

Low-Frequency Noise in Millimeter-Wave Si/SiGe Heterojunction Bipolar Transistors

R. Plana, B. Van Haaren, J.P. Roux, L. Escotte, A. Gruhle, H. Dietrich and J. Graffeuil. "Low-Frequency Noise in Millimeter-Wave Si/SiGe Heterojunction Bipolar Transistors." 1995 MTT-S International Microwave Symposium Digest 95.3 (1995 Vol. III [MWSYM]): 1431-1434.

In this paper we report on the low-frequency (L.F) noise properties of Si/SiGe HBT's. Our results indicate that these devices exhibit very interesting L.F noise performance which compares well with those obtained on BJT Si. However further improvements of the input referred noise current are still needed and our investigations show that they could be achieved through a reduction of the recombination processes at the Emitter-Base heterojunction and at the emitter periphery

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